



8-Output PCIe Gen 6 Clock Generator For Automotive Applications

Description

The DIODES PI6CG338Q is an 8-output very low power PCIe® Gen 1/Gen 2/Gen 3/Gen 4/Gen 5/Gen 6 clock generator. It uses 25MHz crystal or CMOS reference as an input to generate the 100MHz low power differential HCSL outputs with on-chip terminations. The on-chip termination can save 32 external resistors and make layout easier. An additional buffered reference output is provided to serve as a low noise reference for other circuitry.

It uses Diodes' proprietary PLL design to achieve very low jitter that meets PCIe Gen 1/Gen 2/Gen3 /Gen 4/Gen 5/Gen 6 requirements. It also provides various options such as different slew rate and amplitude through SMBUS so that users can configure the device easily to get the optimized performance for their individual boards. The device also supports selectable spread-spectrum options to reduce EMI for various applications.

Block Diagram



Features

- 3.3V Supply Voltage
- Crystal/CMOS Input: 25 MHz
- 8 Differential Low Power HCSL Outputs with On-chip • Termination
- Individual Output Enable •
- Reference CMOS Output
- Programmable Slew Rate and Output Amplitude for Each • Output
- Differential Outputs Blocked Until PLL is Locked ٠
- Selectable 0%, -0.25% or -0.5% Spread on Differential Outputs ٠
- Strapping Pins or SMBus for Configuration
- Differential Output-To-Output Skew <60ps
- Very-Low Jitter Outputs
 - PCIe 6.0 Common Clock (RMS) Jitter <0.04ps</p>
 - Differential Cycle-To-Cycle Jitter <50ps
- PCIe Gen 1/Gen 2/Gen 3/Gen 4/Gen 5/Gen 6 Compliant
- Supports Automotive Grade 2
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The PI6CG338Q is suitable for automotive applications • requiring specific change control; this part is AEC-Q100 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

- Packaging (Pb-free & Green):
 - 48-contact, 6×6mm (ZLW)

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free. 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.





Pin Configuration



Pin Description

Pin #	Pin Name	Ту	pe	Description
				Latched select input to select spread spectrum amount at initial power up.
1	SS_SEL_TRI	Input	Tri-level	1 = -0.5% spread, M = Spread Off, 0 = Spread Off. This pin has both in- ternal pull-up and pull-down. Refer to SMBUS byte_1 bit 4, 3 = '01' to get -0.25% spread.
2	GND_XTAL	Power		Ground for oscillator circuit
3	XTAL_IN/CLK	Input		Crystal input or CMOS reference input
4	XTAL_OUT	Output		Crystal output
5	V _{DD} _OSC	Power		Power supply for oscillator circuitry, nominal 3.3V
6	V _{DD} _REFOUT	Power		Power supply for buffered CMOS output
7	SADR/REFOUT	Input/ Output	CMOS	Latch to select SMBus Address or LVCMOS REFOUT. This pin has an internal pull-down
8	GND_REFOUT	Power		Ground for REFOUT
9	GND_DIG	Power		Ground for digital circuitry
10	SCLK	Input	CMOS	SMBUS clock input, 3.3V tolerant
11	SDATA	Input/ Output	CMOS	SMBUS Data line, 3.3V tolerant
12	V _{DD} _DIG	Power		Power supply for digital circuitry, nominal 3.3V
13, 21, 31, 39, 47	V _{DDO}	Power		Power supply for differential outputs
14	OE0#	Input	CMOS	Active low input for enabling Q0 pair. This pin has an internal pull-down. 1 =disable outputs, 0 = enable outputs





Pin #	Pin Name	Ту	pe	Description
15	Q0+	Output	HCSL	Differential true clock output
16	Q0-	Output	HCSL	Differential complementary clock output
17	OE1#	Input	CMOS	Active low input for enabling Q1 pair. This pin has an internal pull- down. 1 =disable outputs, 0 = enable outputs
18	Q1+	Output	HCSL	Differential true clock output
19	Q1-	Output	HCSL	Differential complementary clock output
20, 38	V _{DD}	Power		Power supply, nominal 3.3V
22, 40	GND	Power		Ground
23	Q2+	Output	HCSL	Differential true clock output
24	Q2-	Output	HCSL	Differential complementary clock output
25	OE2#	Input	CMOS	Active low input for enabling Q2 pair. This pin has an internal pull- down. 1 =disable outputs, 0 = enable outputs
26	Q3+	Output	HCSL	Differential true clock output
27	Q3-	Output	HCSL	Differential complementary clock output
28	OE3#	Input	CMOS	Active low input for enabling Q3 pair. This pin has an internal pull- down. 1 =disable outputs, 0 = enable outputs
29	GNDA	Power		Ground for analog circuitry
30	V _{DDA}	Power		Power supply for analog circuitry
32	Q4+	Output	HCSL	Differential true clock output
33	Q4-	Output	HCSL	Differential complementary clock output
34	OE4#	Input	CMOS	Active low input for enabling Q4 pair. This pin has an internal pull- down. 1 =disable outputs, 0 = enable outputs
35	Q5+	Output	HCSL	Differential true clock output
36	Q5-	Output	HCSL	Differential complementary clock output
37	OE5#	Input	CMOS	Active low input for enabling Q5 pair. This pin has an internal pull- down. 1 =disable outputs, 0 = enable outputs
41	Q6+	Output	HCSL	Differential true clock output
42	Q6-	Output	HCSL	Differential complementary clock output
43	OE6#	Input	CMOS	Active low input for enabling Q6 pair. This pin has an internal pull- down. 1 =disable outputs, 0 = enable outputs
44	Q7+	Output	HCSL	Differential true clock output
45	Q7-	Output	HCSL	Differential complementary clock output
46	OE7#	Input	CMOS	Active low input for enabling Q7 pair. This pin has an internal pull- down. 1 =disable outputs, 0 = enable outputs
48	PD#	Input	CMOS	Input notifies device to sample latched inputs and start up on first high assertion. Low enters Power Down Mode, subsequent high assertions exit Power Down Mode. This pin has internal pull-up resistor.





SMBus Address Selection Table

	SADR	Address	+Read/Write Bit
	0	1101000	Х
State of SADK on first application of PD#	1	1101010	Х

Power Management Table⁽³⁾

PD#	SMBus OE bit	OEn#	Qn+	Qn-	REFOUT
0	Х	Х	Low ⁽¹⁾	Low ⁽¹⁾	HiZ ⁽²⁾
1	1	0	Running	Running	Running
1	1	1	Disabled ⁽¹⁾	Disabled ⁽¹⁾	Running
1	0	Х	Disabled ⁽¹⁾	Disabled ⁽¹⁾	Disabled ⁽⁴⁾

Note:

1. The output state is set by B11[1:0] (Low/Low default)

2. REF is Hi-Z until the 1st assertion of PD# high. After this, when PD# is low, REF is disabled. If Byte 3, bit 5 = 1, then REF is running

3. Input High/ Low defined at default values for device

4. See SMBUs Byte 3, bit 4





Maximum Ratings

(Above which useful life may be impaired. For user guidelines, not tested.)	
Storage Temperature65°C to +150°C	Note:
Supply Voltage to Cround Detential V 0.5V to 14.6V	Stresses greater than those listed under MAXIMUM RAT-
Supply voltage to Ground Potential, v DD_{XX} 0.3 v to +4.0 v	INGS may cause permanent damage to the device. This is
Input Voltage –0.5V to V_{DD} +0.5V, not exceed 4.6V	a stress rating only and functional operation of the device
SMBus, Input High Voltage	at these or any other conditions above those indicated in
ESD Protection (HBM)	the operational sections of this specification is not implied.
Max Junction Temperature+125°C	tended periods may affect reliability.

Operating Conditions

Temperature = T_A; Supply voltages per normal operation conditions; See test circuits for the load conditions

Symbol	Parameters	Conditions	Min.	Тур.	Max.	Units
V _{DD} , V _{DDA} , V _{DD} OSC, V _{DD} DIG,	Power Supply Voltage		3.135	3.3	3.465	V
V _{DDO}	Output Power Supply Voltage		1.0	3.3	3.465	V
V _{DD_RE-} fout	Reference Output Power Supply Voltage		3.135	3.3	3.465	V
I _{DDA}	Analog Power Supply Current	All outputs active @100MHz		22	25	mA
I _{DD}	Power Supply Current	All V_{DD} , except V_{DDA} and V_{DDO} , All outputs active @100MHz		20	32	mA
I _{DDO}	Power Supply Current for Outputs ⁽³⁾	All outputs active @100MHz		29	34	mA
I _{DDA_WL}	Analog Power Supply Wake-on- LAN ⁽¹⁾ Current	Q outputs off, REF output running		0.5	1	mA
I _{DD_WL}	Power Supply Wake-on-LAN ⁽¹⁾ Current	All V_{DD} , except V_{DDA} and V_{DDO} , Q outputs off, REF output running		3	6	mA
I _{DDO_WL}	Power Supply Wake-on-LAN ⁽¹⁾ Current for Outputs	Q outputs off, REF output running		0.04	0.1	mA
I _{DDA_PD}	Analog Power Supply Power Down ⁽²⁾ Current	All outputs off		0.5	1	mA
I _{DD_PD}	Power Supply Power Down ⁽²⁾ Current	All outputs off		1	2	mA
I _{DDO_PD}	Power Supply Current Power Down ⁽²⁾ for Outputs	All outputs off		0.05	0.1	mA
T _A	Ambient Temperature	Automotive grade	-40		105	°C

Note:

1. Wake-on-LAN mode: PD# = '0' Byte 3, bit 5 = '1'

2. Power down mode: PD# = '0' Byte 3, bit 5 = '0'

3. Output drive 5 inch trace.





Input Electrical Characteristics

Symbol	Parameters	Conditions	Min.	Тур.	Max.	Units
R _{pu}	Internal pull up resistance			120		KΩ
R _{dn}	Internal pull down resistance			120		KΩ
C _{XTAL}	Internal capacitance on X_IN and X_OUT pins			8		pF
L _{PIN}	Pin inductance				7	nH

Crystal Characteristic

Parameters	Description	Min.	Тур	Max.	Units
OSCmode	Mode of Oscillation	F	n. Typ Max. Fundamental 25 50 8 7		
FREQ	Frequency		25		MHz
ESR ⁽¹⁾	Equivalent Series Resistance			50	Ω
Cload	Load Capacitance		8		pF
Cshunt	Shunt Capacitance			7	pF
	Drive Level			200	uW

Note:

1. ESR value is dependent upon frequency of oscillation

SMBus Electrical Characteristics

Temperature = T_A ; Supply voltages per normal operation conditions; See test circuits for the load conditions

Symbol	Parameters	Conditions	Min.	Тур.	Max.	Units
V _{DDSMB}	Nominal bus voltage		2.7		3.6	V
		SMBus, $V_{DDSMB} = 3.3V$	2.1		3.6	
V _{IHSMB}	SMBus Input High Voltage	SMBus, V _{DDSMB} < 3.3V	0.65 V _{DDSMB}			V
17	SMBus Input Low Voltage	SMBus, $V_{DDSMB} = 3.3V$			0.8	V
V ILSMB		SMBus, V _{DDSMB} < 3.3V			0.8	
I _{SMBSINK}	SMBus sink current	SMBus, at V _{OLSMB}	4			mA
VOLSMB	SMBus Output Low Voltage	SMBus, at I _{SMBSINK}			0.4	V
f _{MAXSMB}	SMBus operating frequency	Maximum frequency			500	kHz
t _{RMSB}	SMBus rise time	(Max V _{IL} - 0.15) to (Min V _{IH} + 0.15)			1000	ns
t _{FMSB}	SMBus fall time	(Min V_{IH} + 0.15) to (Max V_{IL} - 0.15)			300	ns





Spread Spectrum Characteristic

Temperature = T_A; Supply voltages per normal operation conditions; See test circuits for the load conditions

Symbol	Parameters	Conditions	Min.	Typ.	Max.	Units
f _{MOD}	SS Modulation Frequency	Triangular modulation	30	31.8	33	kHz

LVCMOS DC Electrical Characteristics

Temperature = T_A; Supply voltages per normal operation conditions; See test circuits for the load conditions

Symbol	Parameters	Conditions	Min.	Тур.	Max.	Units
V _{IH}	Input High Voltage	Single-ended inputs, except SMBus	0.75 V _{DD}		V _{DD} +0.3	V
V _{IM}	Input Mid Voltage	SS_SEL_TRI	$0.4 V_{DD}$	$0.5 V_{\rm DD}$	$0.6V_{DD}$	V
V _{IL}	Input Low Voltage	Single-ended inputs, except SMBus	-0.3		0.25 V _{DD}	V
I _{IH}	Input High Current	Single-ended inputs, $V_{IN} = V_{DD}$			5	μA
I _{IL}	Input Low Current	Single-ended inputs, $V_{IN} = 0V$	-5			μA
I _{IH}	Input High Current	Single-ended inputs with pull up / pull down resistor, $\rm V_{IN}$ = $\rm V_{DD}$			50	μA
I _{IL}	Input Low Current	Single-ended inputs with pull up / pull down resistor, $\rm V_{IN}$ = 0V	-50			μA
V _{OH}	Output High Voltage	REFOUT, except SMBus; I _{OH} = -2mA	0.8 x V _{DD} _ Refout			V
V _{OL}	Output Low Voltage	REFOUT, except SMBus; I _{OL} = 2mA			0.2 x V _{DD} _ refout	V
R _{OUT}	CMOS Output impedance			20		Ω
C _{IN}	Input Capacitance		1.5		5	pF

LVCMOS AC Characteristics

femperature = T _A ; Supply voltages per normal operation conditions; See test circuits for the load conditions								
Symbol	Parameters	Conditions	Min.	Тур.	Max.	Units		
f _{INPUT}	Input Frequency	XTAL_IN/CLK		25		MHz		
t _{RIN}	Input rise time	Single-ended inputs			5	ns		
t _{FIN}	Input fall time	Single-ended inputs			5	ns		
t _{STAB}	Clock stabilization	From Power-Up and after input clock stabi- lization or de-assertion of PD# to 1st clock		0.75	1	ms		





Symbol	Parameters	Conditions	Min.	Тур.	Max.	Units
t _{OELAT}	Output enable latency	Q start after OE# assertion Q stop after OE# deassertion	1		3	clocks
t _{PDLAT}	PD# de-assertion	Differential outputs enable after PD# de- assertion		25	300	us
t _{PERIOD}	REFOUT clock period	REFOUT, assume input is at 25MHz		40		ns
f _{ACC}	REFOUT frequency accuracy ⁽¹⁾	REFOUT, long term accuracy to input		0		ppm
		Byte 3 = 1F, 20% to 80% of V_{DDREF}	0.9	1.4	2	V/ns
t _{SLEW}		Byte 3 = 5F, 20% to 80% of V _{DDREF}	1.5	2.4	3.2	V/ns
	REFOUT siew rate ⁽¹⁾	Byte 3 = 9F, 20% to 80% of V _{DDREF}	2	3	3.8	V/ns
		Byte 3 = DF, 20% to 80% of V _{DDREF}	itionsMin.Typ.Max.t after OE# assertion13after OE# deassertion13ential outputs enable after PD# de- on25300UT, assume input is at 25MHz4040UT, long term accuracy to input0 $-$ = 1F, 20% to 80% of VDREF0.91.42= 5F, 20% to 80% of VDREF1.52.43.2= 9F, 20% to 80% of VDREF233.8= DF, 20% to 80% of VDREF2.33.24/DD /2 V, driven by a Xtal455055/DD /2 V, driven by an external-20+2/DD /2 V, driven by a Xtal0.160.33at to 5MHz, SSC off, driven by a Xtal0.91.5offset, driven by a Xtal-149-135offset to Nyquist, driven by a Xtal-158-140	V/ns		
t _{DC}	REFOUT Duty Cycle ⁽¹⁾	$V_{\rm T} = V_{\rm DD}$ /2 V, driven by a Xtal	45	50	55	%
t _{DCDIS}	REFOUT Duty Cycle Distor- tion	$V_{\rm T}$ = $V_{\rm DD}$ /2 V, driven by an external source	-2	0	+2	%
t _{JITCC}	REFOUT cycle-cycle jitter	$V_{\rm T} = V_{\rm DD}$ /2 V, driven by a Xtal		70	150	ps
		12kHz to 5MHz, SSC off, driven by a Xtal		0.16	0.3	ps
IJITPH	REFOUT Phase Jitter, RMS	12kHz to 5MHz, SSC on, driven by a Xtal		0.9	1.5	ps
		1kHz offset, driven by a Xtal		-149	-135	dBc/Hz
J ITN	Noise iloor	10kHz offset to Nyquist, driven by a Xtal		-158	-140	dBc/Hz

Note:

1. Guaranteed by design and characterization, not 100% tested in production

HCSL Output Characteristics

Temperature = T_A; Supply voltages per normal operation conditions; See test circuits for the load conditions

Symbol	Parameters	Condition	Min.	Тур.	Max.	Units
V _{OH}	Output Voltage High ⁽¹⁾	Statistical measurement on single-ended	660	784	850	mV
V _{OL}	Output Voltage Low ⁽¹⁾	signal using oscilloscope math function	-150		150	mV
V _{OMAX}	Output Voltage Maximum ⁽¹⁾	Measurement on single ended signal using		816	1150	mV
V _{OMIN}	Output Voltage Minimum ⁽¹⁾	absolute value	-300	-42		mV
V _{OC}	Output Cross Voltage ^(1,2,4)		250	430	550	mV
DV _{OC}	V _{OC} Magnitude Change ^(1,2,5)			30	140	mV

Note:

1. At default SMBUS amplitude settings

2. Guaranteed by design and characterization, not 100% tested in production

3. Measured from differential waveform

4. This one is defined as voltage where Q+ = Q- measured on a component test board and only applied to the differential rising edge

5. The total variation of all Vcross measurements in any particular system. This is a subset of Vcross_min/max allowed.



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PI6CG338Q

HCSL Output AC Characteristics

Temperature	$= T_A$; Supply voltages per norma	l operation conditions; See test circuit	ts for the	load conc	litions		1
Symbol	Parameters	Condition	Min.	Тур.	Max.	Spec Limit	Units
fout	Output Frequency			100			MHz
4	(1,2,3)	Scope averaging on fast setting	2.5	3.2	4		V/ns
ι _{RF}	Siew rate () //	Scope averaging on slow setting	2.2	3	3.7		V/ns
Dt _{RF}	Slew rate matching ^(1,2,4)	Scope averaging on		7	15		%
t _{DC}	Duty Cycle ^(1,2)	Measured differentially, PLL Mode	45	50	55		%
t _{SKEW}	Output Skew ^(1,2)	Averaging on, $V_T = 50\%$		20	60		ps
tj _{c-c}	Cycle to cycle jitter ^(1,2)			20	50		ps
t _{DC} I t _{SKEW} C tj _{c-c} C tj _{pHASE} I		PCIe 1.0 ⁽⁶⁾ (2.5 Gb/s)		20	30	86	ps(p-p)
		PCIe 2.0 (5 Gb/s)		0.5	0.6	3.1	ps
43	Integrated Phase Jitter (RMS)	PCIe 3.0 (8 Gb/s)		0.32	0.42	1.0	ps
UPHASE	(1,5)	PCIe 4.0 (16 Gb/s)		0.32	0.4	0.5	ps
		PCIe 5.0 (32 Gb/s)		0.05	0.06	0.15	ps
		PCIe 6.0 (64Gb/s)		0.03	0.04	0.1	ps
tj _{PH-SRISG2}	Integrated Phase Jitter (RMS)	PCIe 2.0 (5 Gb/s)		0.6	0.92	N/A	ps
tj _{PH-SRISG3}	Integrated Phase Jitter (RMS)	PCIe 3.0 (8 Gb/s)		0.5	0.6	N/A	ps
tj _{PH-SRISG4}	Integrated Phase Jitter (RMS)	PCIe 4.0 (16 Gb/s)		0.4	0.5	N/A	ps
tj _{PH-SRISG5}	Integrated Phase Jitter (RMS)	PCIe 5.0 (32 Gb/s)		0.06	0.07	N/A	ps
tj _{PH-SRISG6}	Integrated Phase Jitter (RMS)	PCIe 6.0 (64Gb/s)		0.04	0.05	N/A	ps

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Note:

1. Guaranteed by design and characterization—not 100% tested in production.

2. Measured from differential waveform.

3. Slew rate is measured through the Vswing voltage range centered around differential 0V, within ±150mV window.

4. It is measured using a \pm 75mV window centered on the average cross point.

5. See http://www.pcisig.com for complete specs.

6. Sample size of at least 100k cycles. This can be extrapolated to 108ps pk-pk @ 1M cycles for a BER of 10^{-12} .





(N+X-1)

SMBus Serial Data Interface

The PI6CG338Q is a slave only device that supports block read and block write protocol using a single 7-bit address and read/write bit as shown below.

Read and write block transfers can be stopped after any complete byte transfer.

Address Assignment

A6	A5	A4	A3	A2	A1	A0	R/W
1	1	0	1	0	SADR	0	1/0

Note: SMBus address is latched on SADR pin

How to Write

1 bit	7 bits	1 bit	1 bit	8 bits	1 bit	8 bits	1 bit	8 bits	1 bit	8 bits	1 bit	1 bit
Start bit	Add.	W(0)	Ack	Beginning Byte loca- tion = N	Ack	Data Byte count = X	Ack	Beginning Data Byte (N)	Ack	 Data Byte (N+X-1)	Ack	Stop bit

How to Read

1 bit	7 bits	1 bit	1 bit	8 bits	1 bit	1 bit	7 bits	1 bit	1 bit	8 bi	ts	1 bit	8 b i	its	1 bit
Start bit	Address	W(0)	Ack	Beginning Byte loca- tion = N	Ack	Repeat Start bit	Address	R(1)	Ack	Data coun	Byte t = X	Ack	Beg Data (N)	inning a Byte	Ack
											8 bit	8		1 bit	1 bit
											Data I	Byte		NAck	Stop bit

Byte 0: Output Enable Register

Bit	Control Function	Description	Туре	Power Up Condition	0	1
7	Q7_OE	Q7 output enable	RW	1		Pin Control
6	Q6_OE	Q6 output enable	RW	1		Pin Control
5	Q5_OE	Q5 output enable	RW	1		Pin Control
4	Q4_OE	Q4 output enable	RW	1	Soo P11[1.0]	Pin Control
3	Q3_OE	Q3 output enable	RW	1		Pin Control
2	Q2_OE	Q2 output enable	RW	1		Pin Control
1	Q1_OE	Q1 output enable	RW	1		Pin Control
0	Q0_OE	Q0 output enable	RW	1		Pin Control

Note:

1. A low on these bits will override the OE# pins and force the differential outputs to the state indicated by B11[1:0] (Low/ Low default)





B	vte	1:	SS	Spread	S	pectrum	and	Control	Register
-				opicad	-				Register

Bit	Control Function	Description	Туре	Power Up Condition	0	1
7	SSENRB1	SS Enable Readback Bit1	R	Latch	'00' for SS_SEL_	_TRI = '0',
6	SSENRB0	SS Enable Readback Bit0	R	Latch	'10' for SS_SEL_ '11' for SS_SEL_	_TRI = 'M' _TRI = '1'
5	SSEN_SWCTR	Enable SW control of SS	RW	0	Values in B1[7:6] control SS amount	Values in B1[4:3] control SS amount
4	SSENSW1	SS enable SW control Bit1	RW ⁽¹⁾	0	'00' = SS off, '01	' = -0.25% SS,
3	SSENSW0	SS enable SW control Bit0	RW ⁽¹⁾	0	'10' = SS off, '11'	= -0.5% SS
2	Reserved			1		
1	Amplitude1	Control output amplitudo	RW	1	'00' = 0.6V, '01' =	= 0.68V, '10' =
0	Amplitude0	Control output amplitude	RW	0	0.75V, '11' = 0.85	5V

Note:

1. Spread must be selected OFF or ON with the hardware latch pin. These bits should not be used to turn spread ON or OFF after power up. These bits can be used to change the spread amount, and B1[5] must be set to a 1 for these bits to have any effect on the part. If These bits are used to turn spread OFF or ON, the system will need to be reset.

Byte 2: Differential Output Slew Rate Control Register

Bit	Control Function	Description	Туре	Power Up Condition	0	1
7	SLEWRATECTR_Q7	Control slew rate of Q7	RW	1	Slow setting	Fast setting
6	SLEWRATECTR_Q6	Control slew rate of Q6	RW	1	Slow setting	Fast setting
5	SLEWRATECTR_Q5	Control slew rate of Q5	RW	1	Slow setting	Fast setting
4	SLEWRATECTR_Q4	Control slew rate of Q4	RW	1	Slow setting	Fast setting
3	SLEWRATECTR_Q3	Control slew rate of Q3	RW	1	Slow setting	Fast setting
2	SLEWRATECTR_Q2	Control slew rate of Q2	RW	1	Slow setting	Fast setting
1	SLEWRATECTR_Q1	Control slew rate of Q1	RW	1	Slow setting	Fast setting
0	SLEWRATECTR_Q0	Control slew rate of Q0	RW	1	Slow setting	Fast setting





Byte 3: REF Control Register

Bit	Control Function	Description	Туре	Power Up Condition	0	1		
7			RW	0	'00' = 1.4V/ns '0	1' = 2.4V/ns,		
6	REFSLEWRATE	Siew rate control for REF	RW	1	'10' = 3V/ns, '11' = 3.2V/ns			
5	REF_PDSTATE	Wake-on-Lan enable for REF	RW	0	REF = Dis- abled in PD state ⁽¹⁾	REF = run- ning in PD state		
4	REF_OE	Output enable for REF	RW	1	REF = Dis- abled ⁽¹⁾	REF = run- ning		
3	Reserved			1				
2	Reserved			1				
1	Reserved			1				
0	Reserved			1				

Note:

1. The disabled state depends on Byte11[1:0]. '00' = Low, '01'=HiZ, '10'=Low, '11'=High

Byte 4: Reserved

Bit	Control Function	Description	Туре	Power Up Condition	0	1
7:0	Reserved			0x40		

Byte 5: Revision and Vendor ID Register

Bit	Control Function	Description	Туре	Power Up Condition	0	1	
7	RID3		R	0	rev = 0000		
6	RID2	evision ID	R	0			
5	RID1		R	0			
4	RID0		R	0			
3	PVID3		R	0			
2	PVID2		R	0	Diodes = 0011		
1	PVID1	vendor ID	R	1			
0	PVID0		R	1			





Byte 6: Device Type/Device ID Register

Bit	Control Function	Description	Туре	Power Up Condition	0	1
7	DTYPE1	Davies type	R	0	'00' = CG, '01' =	ZDB,
6	DTYPE0	evice type	R	0	'10' = Reserve, '11' = NZDB	
5	DID5		R	0	001000 binary, 08Hex	
4	DID4		R	0		
3	DID3	Device ID	R	1		
2	DID2	Device ID	R	0		
1	DID1	-	R	0		
0	DID0		R	0		

Byte 7: Byte Count Register

Bit	Control Function	Description	Туре	Power Up Condition	0	1	
7	Reserved			0			
6	Reserved			0			
5	Reserved			0			
4	BC4		RW	0			
3	BC3		RW	1	Writing to this register will configure how many bytes will be read back, default is 8 bytes		
2	BC2	Byte count programming	RW	0			
1	BC1		RW	0			
0	BC0		RW	0			

Byte 8 and 9: Reserved

Bit	Control Function	Description	Туре	Power Up Condition	0	1
7:0	Reserved			B8 = 0x36		
				B9 = 0x00		

Byte 10: PD Restore

Bit	Control Function	Description	Туре	Power Up Condition	0	1
7	Reserved			0		
6	PD Restore	PD Restore to default configuration	RW	1	Clear PD Config	Keep PD Config
5:0	Reserved			0		





Byte 11: Stop Control

Bit	Control Function	Description	Туре	Power Up Condition	0	1
7:2	Reserved			0		
1	STP1	True/ Compliment DIF Output Disable Sate	RW	0	00= Low/Low	10= High/ Low
0	STP0		RW	0	01= HiZ/HiZ	11= Low/High

Byte 12: Impedance Control

Bit	Control Function	Description	Туре	Power Up Condition	0	1	
7	Q3_Zout1	Q3 Zout	RW	-			
6	Q3_Zout0	Q3 Zout	RW				
5	Q2_Zout1	Q2 Zout	RW		00 = Reserved		
4	Q2_Zout0	Q2 Zout	RW	10	$01 = 85\Omega$		
3	Q1_Zout1	Q1 Zout	RW	10	$10 = 100\Omega$		
2	Q1_Zout0	Q1 Zout	RW	-	11 = Reserved		
1	Q0_Zout1	Q0 Zout	RW				
0	Q0_Zout0	Q0 Zout	RW				

Byte 13: Impedance Control

Bit	Control Function	Description	Туре	Power Up Condition	0	1	
7	Q7_Zout1	Q7 Zout	RW		00 = Reserved		
6	Q7_Zout0	Q7 Zout	RW				
5	Q6_Zout1	Q6 Zout	RW				
4	Q6_Zout0	Q6 Zout	RW		$01 = 85\Omega$		
3	Q5_Zout1	Q5 Zout	RW	10	10 = 100Ω 11 = Reserved		
2	Q5_Zout0	Q5 Zout	RW				
1	Q4_Zout1	Q4 Zout	RW				
0	Q4_Zout0	Q4 Zout	RW				





Byte 14: OE Termination Control

Bit	Control Function	Description	Туре	Power Up Condition	0	1
7	OE3_term1	OE3 Pull up or down	RW	0	00=None	10= Pullup
6	OE3_term0	OE3 Pull up or down	RW	1	01=Pulldown	11=Pullup and Down
5	OE2_term1	OE2 Pull up or down	RW	0	00=None	10= Pullup
4	OE2_term0	OE2 Pull up or down	RW	1	01=Pulldown	11=Pullup and Down
3	OE1_term1	OE1 Pull up or down	RW	0	00=None	10= Pullup
2	OE1_term0	OE1 Pull up or down	RW	1	01=Pulldown	11=Pullup and Down
1	OE0_term1	OE0 Pull up or down	RW	0	00=None	10= Pullup
0	OE0_term0	OE0 Pull up or down	RW	1	01=Pulldown	11=Pullup and Down

Byte 15: OE Termination Control

Bit	Control Function	Description	Туре	Power Up Condition	0	1
7	OE7_term1	OE7 Pull up or down	RW	0	00=None	10= Pullup
6	OE7_term0	OE7 Pull up or down	RW	1	01=Pulldown	11=Pullup and Down
5	OE6_term1	OE6 Pull up or down	RW	0	00=None	10= Pullup
4	OE6_term0	OE6 Pull up or down	RW	1	01=Pulldown	11=Pullup and Down
3	OE5_term1	OE5 Pull up or down	RW	0	00=None	10= Pullup
2	OE5_term0	OE5 Pull up or down	RW	1	01=Pulldown	11=Pullup and Down
1	OE4_term1	OE4 Pull up or down	RW	0	00=None	10= Pullup
0	OE4_term0	OE4 Pull up or down	RW	1	01=Pulldown	11=Pullup and Down

Byte 16: Power Good Termination Control

Bit	Control Function	Description	Туре	Power Up Condition	0	1
7:2	Reserved			0x09		
1	PWRGD_PD1	Clock Power Good and Power Down Pull up or – Pull down	RW	1	00=None	10= Pullup
0	PWRGD_PD0		RW	0	01=Pulldown	11=Pullup and Down





Byte 17: Reserved

Byte 18: Enable Pin Control

Bit	Control Function	Description	Туре	Power Up Condition	0	1
7	OE7_Enable	Sets Enable High or Low	RW	0	Enable = Low	Enable = High
6	OE6_Enable	Sets Enable High or Low	RW	0	Enable = Low	Enable = High
5	OE5_Enable	Sets Enable High or Low	RW	0	Enable = Low	Enable = High
4	OE4_Enable	Sets Enable High or Low	RW	0	Enable = Low	Enable = High
3	OE3_Enable	Sets Enable High or Low	RW	0	Enable = Low	Enable = High
2	OE2_Enable	Sets Enable High or Low	RW	0	Enable = Low	Enable = High
1	OE1_Enable	Sets Enable High or Low	RW	0	Enable = Low	Enable = High
0	OE0_Enable	Sets Enable High or Low	RW	0	Enable = Low	Enable = High

Byte 19: Power Down Pin Control

Bit	Control Function	Description	Туре	Power Up Condition	0	1
7:1	Reserved			0		
0	PWRGD_PD	PWRGD_PD Active via Pull up or Pull down	RW	0	Power Down = Low	Power Down = High





Phase Noise Plots

100MHz HCSL Clock (12k to 20MHz)



25MHz CMOS Clock









Figure 1. Low Power HCSL Test Circuit



Figure 2. CMOS REF Test Circuit



Figure 3. Differential Output driving LVDS

Alternate Differential Output Terminations

Component	Receiver with Termination	Receiver without Termination	Unit
R _{1a} , R _{1b}	10,000	140	Ω
R_{2a}, R_{2b}	5,600	75	Ω
C _C	0.1	0.1	μF
V _{CM}	1.2	1.2	V



Figure 4. Power Supply Filter





Crystal Circuit Connection

The following diagram shows PI6CG338Q crystal circuit connection with a parallel crystal. For the CL = 8pF crystal, it is suggested to use C1 = 8pF, C2 = 8pF. C1 and C2 can be adjusted to fine tune to the target ppm of crystal oscillator according to different board layouts based on the following formular in the Crystal Capacitor Calculation diagram.

Crystal Oscillator Circuit



Crystal Capacitor Calculation



Recommended Crystal Specification

Diodes Recommends:

a) FL2500262Q, SMD 3.2x2.5(4P), 25MHz, CL=8pF, ±50ppm, https://www.diodes.com/assets/Datasheets/FL.pdf.

b) FW2500054Q, SMD 2.0x1.6(4P), 25MHz, CL=8pF, ±50ppm, https://www.diodes.com/assets/Datasheets/FW.pdf.

Thermal Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
θ_{JA}	Thermal Resistance Junction to Ambient	Still air			38.15	°C/W
θ _{JC}	Thermal Resistance Junction to Case				24.66	°C/W





Part Marking



YY: Year WW: Workweek 1st X: Assembly Code 2nd X: Fab Code





Packaging Mechanical

48-VQFN (ZLW)



For latest package info.

please check: http://www.diodes.com/design/support/packaging/pericom-packaging/packaging-mechanicals-and-thermal-characteristics/

Ordering Information

Ordering Code	Package Code	Package Description	Operating Temperature
PI6CG338Q2ZLWEX	ZLW	V-QFN6060-48 (SWP)	-40°C to 105°C

Notes:

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free. 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

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4. Q = Automotive Compliant

5. 2 = AEC-Q100 Grade Level

6. E = Pb-free and Green

7. X suffix = Tape/Reel





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